

SNx4HCT125 具有三态输出的四路总线缓冲门

1 特性

- 4.5V 至 5.5V 的工作电压范围
- 高电流可驱动多达 15 个 LSTTL 负载
- 低功耗， I_{CC} 最大值为 80 μ A
- t_{pd} 典型值 = 12ns
- 电压为 5V 时，输出驱动为 ± 6 mA
- 低输入电流，最大值 1 μ A
- 输入兼容 TTL 电压
- 高电流三态输出驱动总线或缓冲存储器地址寄存器

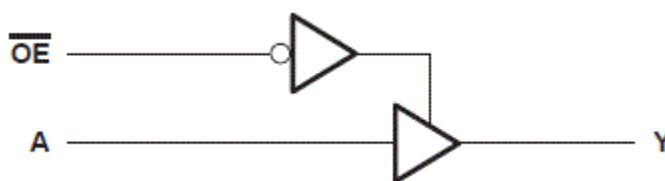
2 说明

SNx4HCT125 包含四个具有 TTL 兼容输入和三态输出的独立缓冲器。每个逻辑门以正逻辑执行布尔函数 $Y = A$ 。

器件信息

器件型号	封装 ⁽¹⁾	封装尺寸 (标称值)
SN74HCT125D	SOIC (14)	8.65mm × 3.90mm
SN74HCT125N	PDIP (14)	19.31mm × 6.35mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



功能方框图



Table of Contents

1 特性	1	7.2 Functional Block Diagram.....	8
2 说明	1	7.3 Device Functional Modes.....	8
3 Revision History	2	8 Power Supply Recommendations	9
4 Pin Configuration and Functions	3	9 Layout	9
5 Specifications	4	9.1 Layout Guidelines.....	9
5.1 Absolute Maximum Ratings.....	4	10 Device and Documentation Support	10
5.2 Recommended Operating Conditions ⁽¹⁾	4	10.1 Documentation Support.....	10
5.3 Thermal Information.....	4	10.2 接收文档更新通知.....	10
5.4 Electrical Characteristics.....	5	10.3 支持资源.....	10
5.5 Switching Characteristics.....	5	10.4 Trademarks.....	10
5.6 Operating Characteristics.....	6	10.5 Electrostatic Discharge Caution.....	10
6 Parameter Measurement Information	7	10.6 术语表.....	10
7 Detailed Description	8	11 Mechanical, Packaging, and Orderable Information	10
7.1 Overview.....	8		

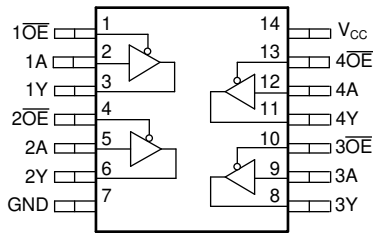
3 Revision History

注：以前版本的页码可能与当前版本的页码不同

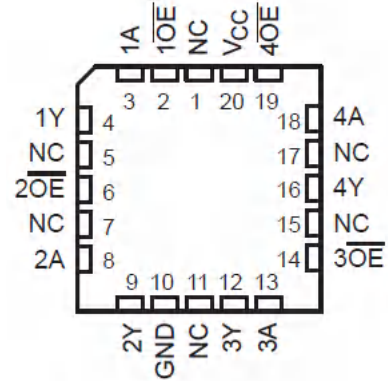
Changes from Revision F (February 2022) to Revision G (October 2022)	Page
• Increased R _{θJA} for packages: D (86 to 138.7); N (80 to 75.3).....	4

Changes from Revision E (August 2003) to Revision F (February 2022)	Page
• 更新了整个文档中的编号、格式、表格、图和交叉参考，以反映现代数据表标准.....	1

4 Pin Configuration and Functions



**D, N, J or W Package
14-Pin SOIC or PDIP
Top View**



NC – No internal connection

**FK Package
20-Pin LCCC
Top View**

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage range	-0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	(V _I < 0 or V _I > V _{CC})		±20 mA
I _{OK}	Output clamp current ⁽²⁾	(V _O < 0 or V _O > V _{CC})		±20 mA
I _O	Continuous output current	(V _O = 0 to V _{CC})		±35 mA
V _{CC} or GND	Continuous current through			±70 mA
T _J	Junction temperature			150 °C
T _{stg}	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 Recommended Operating Conditions⁽¹⁾

		SN54HCT125 ⁽²⁾			SN74HCT125			UNIT
		MIN	NOM	MAX	MIN	NOM	MAX	
V _{CC}	Supply voltage	4.5	5	5.5	4.5	5	5.5	V
V _{IH}	High-level input voltage	V _{CC} = 4.5 V to 5.5 V		2	2		V	
V _{IL}	Low-level input voltage	V _{CC} = 4.5 V to 5.5 V		0.8		0.8	V	
V _I	Input voltage	0	V _{CC}		0	V _{CC}		V
V _O	Output voltage	0	V _{CC}		0	V _{CC}		V
t _t	Input transition rise/fall time	500		500		500	ns	
T _A	Operating free-air temperature	-55	125		-40	85		°C

- (1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report *Implications of Slow or Floating SMOS Inputs*, literature number [SCBA004](#).
- (2) SN54HCT125 is in product preview.

5.3 Thermal Information

THERMAL METRIC		D (SOIC)	N (PDIP)	UNIT
		14 PINS	14 PINS	
R _{θJA}	Junction-to-ambient thermal resistance ⁽¹⁾	138.7	75.3	°C/W
R _{θJC}	Junction-to-case (top) thermal resistance	93.8	68.6	°C/W
R _{θJB}	Junction-to-board thermal resistance	94.7	55.1	°C/W
ψ _{JT}	Junction-to-top characterization parameter	49.1	41.1	°C/W
ψ _{JB}	Junction-to-board characterization parameter	94.3	54.9	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

5.4 Electrical Characteristics

PARAMETER		TEST CONDITIONS ⁽¹⁾	V _{CC} (V)	T _A = 25°C			SN54HCT125 ⁽³⁾		SN74HCT125		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V _{OH}	High-level output voltage	I _{OH} = -20 μA	4.5	4.4	4.499		4.4		4.4	V	
		I _{OH} = -6 mA		3.98	4.3		3.7		3.84		
V _{OL}	Low-level output voltage	I _{OL} = 20 μA	5.5		0.001	0.1		0.1	0.1	V	
		I _{OL} = 6 mA			0.17	0.26		0.4	0.33		
I _I	Input hold current	V _I = V _{CC} or 0	5.5	±0.1	±100		±1000		±1000	nA	
I _{OZ}	Off-state output current	V _o = V _{CC} or 0	5.5	±0.01	±0.5		±10		±5	μA	
I _{CC}	Supply current	V _I = V _{CC} or 0. I _O = 0	5.5		8		160		80	μA	
Δ I _{CC} ⁽²⁾	Supply-current change	One input at 0.5 V or 2.4 V, Other inputs at 0 or V _{CC}	5.5		1.4	2.4		3		2.9	mA
C _i	Input capacitance		4.5 to 5.5		3	10		10 ⁽⁴⁾		10	pF

- (1) V_I = V_{IH} or V_{IL}, unless otherwise noted.
(2) This is the increase in supply current for each input that is at one of the specified TTL voltage levels, rather than 0 V or V_{CC}.
(3) SN54HCT125 is in product preview.
(4) On products compliant to MIL-PRF-38535, this parameter is not production tested.

5.5 Switching Characteristics

C_L = 50 pF. See [Figure 6](#)

PARAMETER		FROM (INPUT)	TO (OUTPUT)	V _{CC} (V)	T _A = 25°C			SN54HCT125 ⁽¹⁾		SN74HCT125		
					MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t _{pd}	Propagation delay	A	Y	4.5		11	20		39		25	ns
				5.5		10	18		35		22	
t _{en}	Enable time	OE	Y	4.5		18	28		42		35	ns
				5.5		15	25		38		31	
t _{dis}	Diable time	OE	Y	4.5		15	26		39		33	ns
				5.5		13	23		35		30	
t _t	Transition time		Any	4.5		8	15		22		19	ns
				5.5		7	14		21		17	

- (1) SN54HCT125 is in product preview.

5.5 Switching Characteristics

C_L = 150 pF. See [Figure 6](#)

PARAMETER		FROM (INPUT)	TO (OUTPUT)	V _{CC} (V)	T _A = 25°C			SN54HCT125 ⁽¹⁾		SN74HCT125		
					MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t _{pd}	Propagation delay	A	Y	4.5		19	36		58		46	ns
				5.5		16	32		48		42	
t _{en}	Enable time	OE	Y	4.5		25	40		60		50	ns
				5.5		21	35		53		43	
t _t	Transition time		Any	4.5		17	42		63		53	ns
				5.5		14	38		57		48	

- (1) SN54HCT125 is in product preview.

5.6 Operating Characteristics

$T_A = 25^\circ\text{C}$

		Test Conditions	TYP	UNIT
C_{pd}	Power dissipation capacitance	No load	35	pF

6 Parameter Measurement Information

t_{pd} is the maximum between t_{PLH} and t_{PHL}

t_t is the maximum between t_{TLH} and t_{THL}

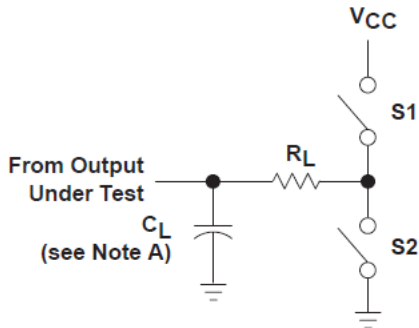


图 6-1. Load Circuit

PARAMETER	R_L	C_L	S1	S2
t_{en}	1 k Ω	50 pF or 150 pF	Open	Closed
			Closed	Open
t_{dis}	1 k Ω	50 pF	Open	Closed
			Closed	Open
t_{pd} or t_t	—	50 pF or 150 pF	Open	Open

图 6-2.

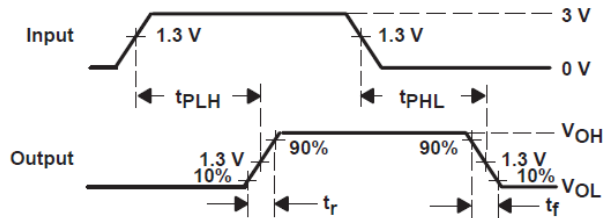


图 6-3. Voltage Waveforms Propagation Delay Times

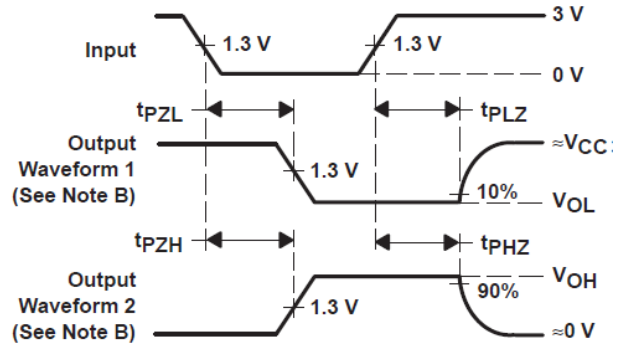


图 6-4. Voltage Waveforms Enable and Disable Times For 3-state Outputs

A. C_L includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.

Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.

C. Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1$ MHz, $Z_O = 50 \Omega$, $t_r = 6$ ns, $t_f = 6$ ns.

D. The outputs are measured one at a time with one input transition per measurement.

E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .

F. t_{PZL} and t_{PZH} are the same as t_{en} .

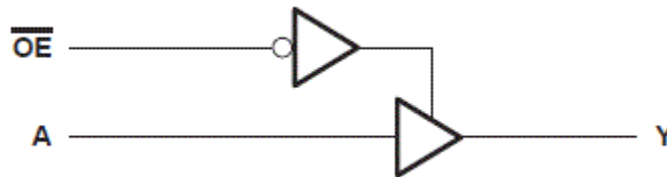
7 Detailed Description

7.1 Overview

These bus buffer gates feature independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (\overline{OE}) input is high.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

7.2 Functional Block Diagram



7.3 Device Functional Modes

表 7-1. Function Table
(each gate)

INPUTS		OUTPUT
OE	A	Y
L	H	H
L	L	L
H	X	Z

8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

9 Layout

9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 Documentation Support

10.1.1 Related Documentation

10.2 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

10.3 支持资源

TI E2E™ [支持论坛](#) 是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [《使用条款》](#)。

10.4 Trademarks

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10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.6 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74HCT125D	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HCT125	Samples
SN74HCT125DE4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HCT125	Samples
SN74HCT125DG4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HCT125	Samples
SN74HCT125DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	HCT125	Samples
SN74HCT125DRE4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HCT125	Samples
SN74HCT125DT	ACTIVE	SOIC	D	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HCT125	Samples
SN74HCT125N	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74HCT125N	Samples
SN74HCT125NE4	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74HCT125N	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCT125DR	SOIC	D	14	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
SN74HCT125DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HCT125DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HCT125DT	SOIC	D	14	250	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCT125DR	SOIC	D	14	2500	366.0	364.0	50.0
SN74HCT125DR	SOIC	D	14	2500	356.0	356.0	35.0
SN74HCT125DR	SOIC	D	14	2500	356.0	356.0	35.0
SN74HCT125DT	SOIC	D	14	250	210.0	185.0	35.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN74HCT125D	D	SOIC	14	50	506.6	8	3940	4.32
SN74HCT125DE4	D	SOIC	14	50	506.6	8	3940	4.32
SN74HCT125DG4	D	SOIC	14	50	506.6	8	3940	4.32
SN74HCT125N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HCT125N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HCT125NE4	N	PDIP	14	25	506	13.97	11230	4.32
SN74HCT125NE4	N	PDIP	14	25	506	13.97	11230	4.32

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



4211283-3/E 08/12

- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 - The 20 pin end lead shoulder width is a vendor option, either half or full width.

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